

Features:

Frequency Range: 17 – 43 GHz

P1dB: 18 dBmPsat: 20 dBmGain: 21 dB

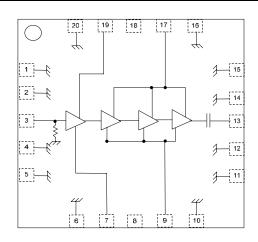
• Vdd =4.5 V (3 V to 5 V)

• Ids = 250 mA (150mA to 300mA)

• Input and Output Fully Matched to 50 Ω

• 2x and 3x Frequency multiplier applications

• Surface Mount, RoHs Compliant QFN 4x4mm package



Functional Block Diagram

Applications:

Communication systems

Microwave instrumentations

Description:

The MMA-174321 is a broadband GaAs MMIC general purpose gain block for 0.1-Watt maximum output power and high gain over full 17 to 43GHz frequency range. This amplifier is able to use as 2x and 3x Frequency multipliers when biased under class-B condition for the first stage.

Absolute Maximum Ratings: (Ta= 25 °C)*

SYMBOL	PARAMETERS	UNITS	Min.	Max.		
Vd1, Vd2	Drain-Supply Voltage	V		5.4		
Vg1	Optional Gate supply Voltage	V	-2	0.5		
Vg2	Optional Gate supply Voltage	V	-2	0.5		
ldd	Total Drain Supply Current	mA		400		
Pin max	RF Input Power	dBm		21		
Toper	Operating Temperature	°C		-40 to +85		
Tch	Channel Temperature	°C		+150		
Tstg	Storage Temperature	°C		-55 to +165		
Tmax	Max. Assembly Temp (60 sec max)	°C		+300		
*Operation of this device above any one of these parameters may cause permanent damage.						

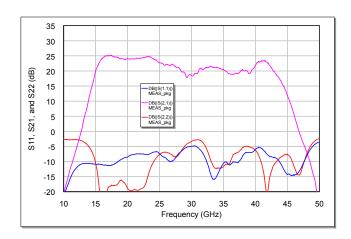
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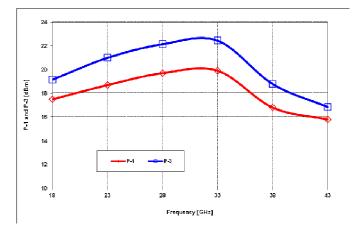
Electrical Specifications:	Vds=4.5V, Vgs=-0.7V,	, Ids=250mA, Ta=25 ℃ Z0=50 ohm			
Parameter	Units	Typical Data			
Frequency Range	GHz	17-43			
Gain (Typ / Min)	dB	21 / 18			
Gain Flatness (Typ / Max)	+/-dB	2.5 / 3			
Input RL(Typ/ Max)	dB	8/5			
Output RL(Typ/ Max)	dB	8/3			
Output P1dB(Typ/Min)	dBm	18/16			
Output IP3 (1)	dBm	26			
Output Psat(Typ/ Min)	dBm	20/17			
Operating Current at P1dB (Typ/ Max)	m A	230 / 250			
Thermal Resistance	°C /W	30			
(1) Output IP3 is measured with two tones at output power of 5 dBm/tone separated by 20 MHz.					



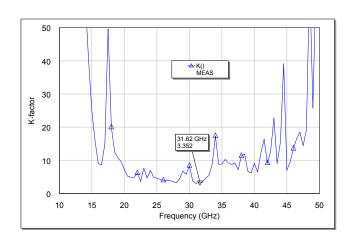
Typical RF Performance: Vds=4.5V, Vgs=-0.7V, Ids=250mA, Z0=50 ohm, Ta=25 °C



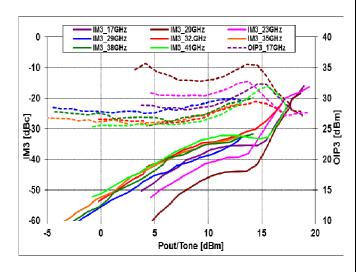
S11[dB], S21[dB], and S22[dB] vs. Frequency



P-1 and Psat vs. Frequency



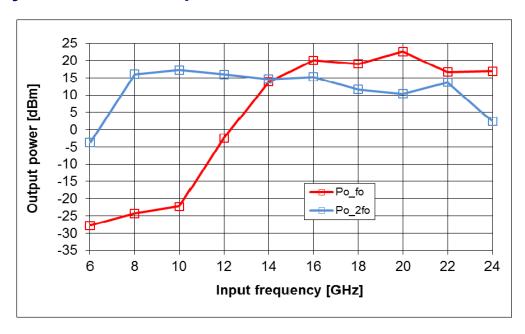
K-factor vs. Frequency



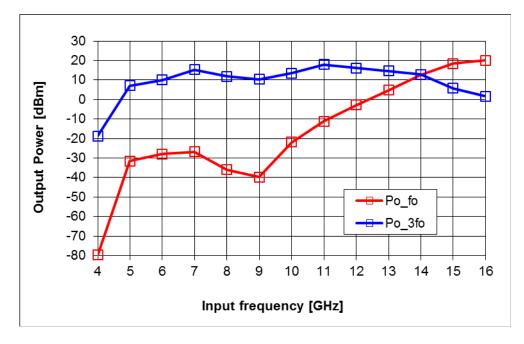
IM3 level [dBc] vs. Input power [dBm/tone]



Frequency 2x and 3x multiplier Data:



Measured 2x multiplier data: Pin=9dBm, Vd1=5V, Vd2=5V, Vg1=-1.4V, Vg2=-0.7V, Id1=1mA, and Id2=163mA

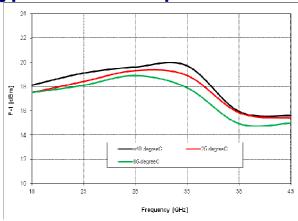


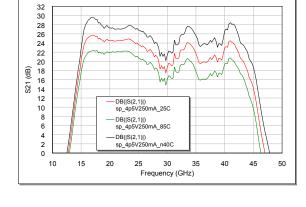
Measured 3x multiplier data: Pin=9dBm, Vd1=1V, Vd2=5V, Vg1=-0.75V, Vg2=-0.75V, Id1=21mA, and Id2=144mA



17-43GHz, 0.1W Gain Block Data Sheet

Typical Over Temperature Performance: Vds=4.5V, Ids=250mA, Z0=50 ohm, Ta=-40, 25, and 85 °C





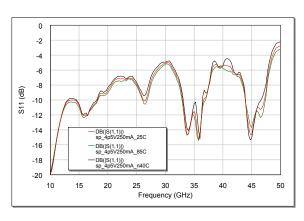
P1 over temperature

24
22
21
22
21
22
21
22
21
22
23
24
24
25
26
28-degreeC

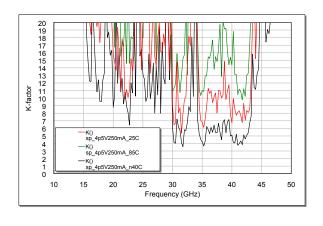
12
10
18
23
29
33
38
43

Frequency [GHz]

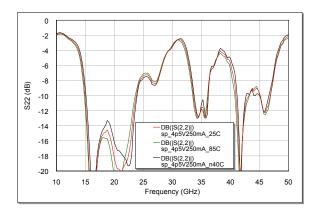
S21(dB) over temperature



P-3 over temperature



S11(dB) over temperature



K-factor over temperature

S22(dB) over Voltage



Applications

The **MMA-174321-M4** MMIC power amplifier is designed for use as a power stage amplifier in microwave transmitters. It is ideally suited for 17 to 43GHz band applications requiring a flat gain response and excellent power performance. This amplifier is packaged in QFN 4X4.

Biasing and Operation

The recommended bias conditions for best performance for the MMA-174321-M4 are VDD = 4.5V, Idsq = 250mA. Performance improvements are possible depending on applications. The drain bias voltage range is 3 to 5V and the quiescent drain current biasing range is 150mA to 300mA. Vg1 is connected to first stages of gate, and Vg2 is connected to following three stages of gates. Muting can be accomplished by setting Vg1 and Vg2 to the pinched-off voltage (Vp=-2V). The gate voltages (Vg1 and Vg2) should be applied prior to the drain voltages (Vd1 and Vd2) during power up and removed after the drain voltages during power down. The RF input port is connected internally to the 50Ω load for ESD protection purpose; therefore, an input decoupling capacitor is needed if the preceding output stage has DC present. The RF output is DC decoupled internally. Typical DC supply connection with bi-passing capacitors for the MMA-174321-M4 is shown in following pages.

Frequency x2 and x3 Multiplier Applications:

MMA-174321-M4 is able to use as a frequency x2 multiplier when biased under Vd1=5V, Vd2=5V, Vg1=-1.4V, Vg2=- 0.7V, Id1=1mA, and Id2=163mA. Optimum input RF power level is +9dBm. Typical measured data is shown in previous page. **MMA-174321-M4** is also able to use as a frequency x3 multiplier when biased under Vd1=1V,

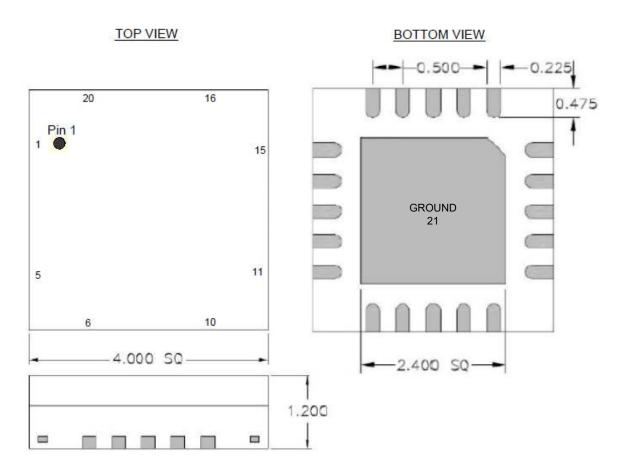
Vd2=5V, Vg1=-0.75V, Vg2=-0.75V, Id1=21mA, and Id2=144mA. Optimum input RF power level is +9dBm. Typical measured data is shown in previous page.

Assembly Techniques

GaAs MMICs are ESD sensitive. ESD preventive measures must be employed in all aspects of storage, handling, and assembly. MMIC ESD precautions, handling considerations, die attach and bonding methods are critical factors in successful GaAs MMIC performance and reliability.



Package Pin-out:

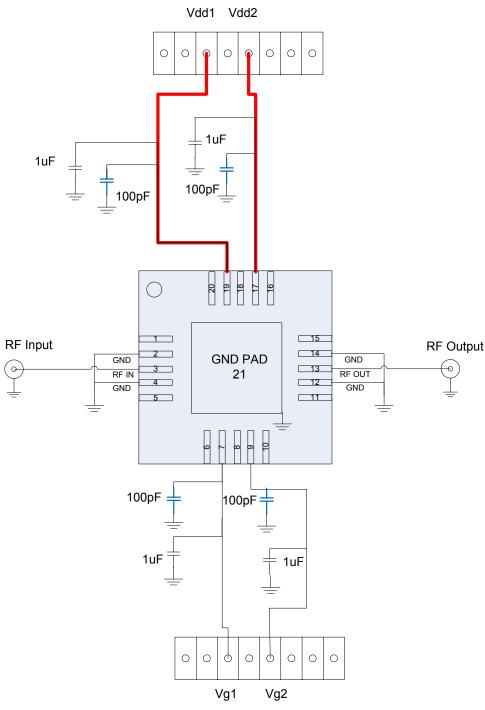


The units are in [mm].

Pin	Description
3	RF Input
13	RF Output
7	Vg1
9	Vg2
19	Vd1
17	Vd2
1, 2, 4, 5 ,6, 10, 11, 12, 14, 15, 16, 20, 21	Ground
8, 18	N/C



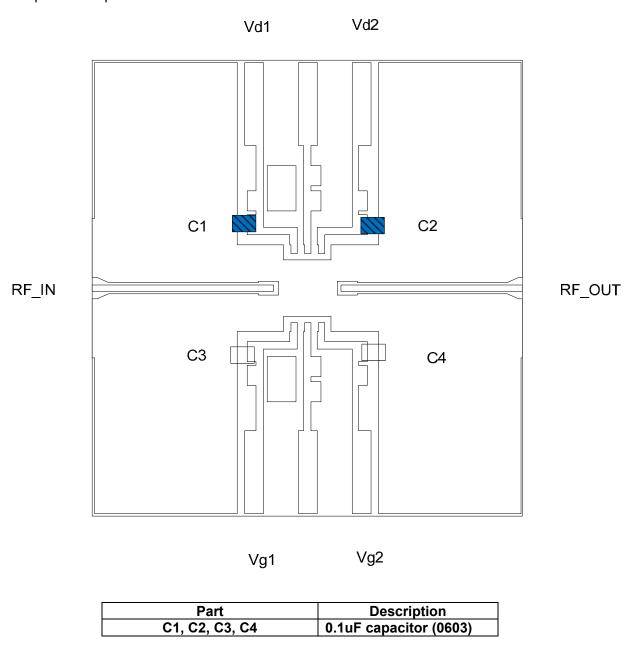
Application Circuit:





Recommended Application Board Design:

Board Material is 10mil (Dielectric) thickness Rogers 4350B with 0.5oz cupper clads. Board is soldered on a gold plated solid cupper block and adequate heat-sinking is required for 1.5W total maximum power dissipation.





Recommended Application Board Design:

Board Material is 10mil (Dielectric) thickness Rogers 4350B with 0.5oz cupper clads. The board material and mounting pattern, as defined in the data sheet, optimizes RF performance and is strongly recommended. An electronic drawing of the land pattern is available upon request from *MwT* Sales & Application Engineering.

